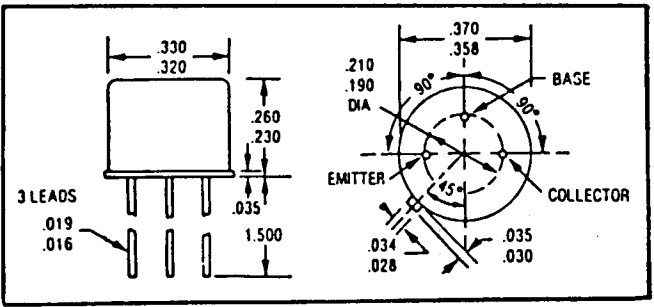


X06141

<h1 style="margin: 0;">2N5094 AND 2N5096</h1> <h2 style="margin: 0;">1 AMP</h2> <h3 style="margin: 0;">HIGH VOLTAGE PNP TRANSISTOR</h3> <h3 style="margin: 0;">450-500 VOLTS</h3>	
<p style="font-size: small; margin: 0;">14830 Valley View Avenue La Mirada, California 90638 (213) 921-9660 TWX 910-583-4807 FAX 213-921-2396</p>	

CASE STYLE W
JEDEC TO-5



FEATURES

- BVCBO TO 500 VOLTS
- LOW SATURATION VOLTAGE
- LOW LEAKAGE AT HIGH TEMPERATURE
- 200°C OPERATING, GOLD EUTECTIC DIE ATTACH
- DESIGNED FOR COMPLEMENTARY USE WITH 2N5095 THRU 2N5097
- 2N5091 AND 2N5093 ALSO AVAILABLE

MAXIMUM RATINGS

Rating	Symbol	2N5094	2N5096	Unit
Collector - Emitter Voltage	V_{CE0}	400	450	Volts
$R_{BE} = 1 \text{ K Ohms}$	V_{CER}	450	500	Volts
Collector - Base Voltage	V_{CBO}	450	500	Volts
Emitter - Base Voltage	V_{EBO}	6.0		Volts
Collector Current	I_C	1.0		Amps
Base Current	I_B	0.5		Amps
Total Device Dissipation @ $T_C = 100^\circ\text{C}$	P_D	2		Watts
Derate above 100 °C		20		mW/°C
Operating and Storage Temperature	T_j, T_{stg}	-65 to +200		°C

THERMAL CHARACTERISTICS

Characteristics	Symbol	Value	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	50	°C/W

ELECTRICAL CHARACTERISTICS

Characteristics	Symbol	Min.	Max.	Unit
Collector - Emitter Breakdown Voltage* ($I_C = 50 \text{ mA dc}$)	BV_{CE0}^*	400 450		Vdc
($I_C = 100 \text{ uA dc}, R_{BE} = 1 \text{ K Ohms}$)	BV_{CER}^*	450 500		Vdc
Collector - Base Breakdown Voltage ($I_C = 100 \text{ uA dc}$)	BV_{CBO}	450 500		Vdc
Emitter - Base Breakdown Voltage ($I_E = 20 \text{ uA dc}$)	BV_{EBO}	6		Vdc

NOTE: All specifications subject to change without notice.

ELECTRICAL CHARACTERISTICS

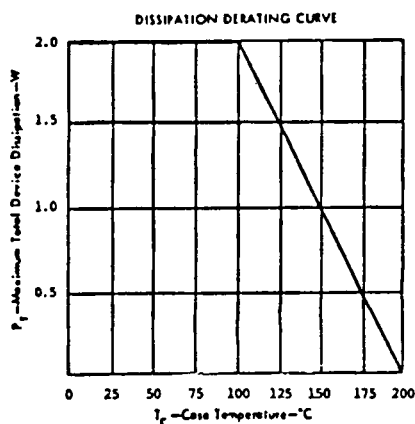
Characteristics	Symbol	Min.	Max.	Unit
Collector Cutoff Current 2N5094 VCB= 450 Vdc 2N5096 VCB= 500 Vdc	I_{CBO}		500	nA dc
Emitter Cutoff Current ($V_{EB} = 4 \text{ Vdc}$)	I_{EBO}		250	nA dc
DC Current Gain* ($I_C = 1 \text{ mAdc}, V_{CE} = 10 \text{ Vdc}$) ($I_C = 25 \text{ mAdc}, V_{CE} = 10 \text{ Vdc}$) ($I_C = 100 \text{ mAdc}, V_{CE} = 15 \text{ Vdc}$)	h_{FE}	20 40 20	200 250 200	
Collector - Emitter Saturation Voltage* ($I_C = 25 \text{ mAdc}, I_B = 2.5 \text{ mAdc}$)	$V_{CE(SAT)}$		3.0	Vdc
Base - Emitter Saturation Voltage* ($I_C = 25 \text{ mAdc}, I_B = 2.5 \text{ mAdc}$)	$V_{BE(SAT)}$		1.0	Vdc
Current - Gain - Bandwidth Product ($I_C = 10 \text{ mAdc}, V_{CE} = 20 \text{ Vdc}, f = 5 \text{ MHz}$)	f_T	20		MHz
Output Capacitance ($V_{CB} = 15 \text{ Vdc}, I_E = 0.1 = 2 \text{ MHz}$)	C_{ob}		20	pf

SWITCHING TIMES

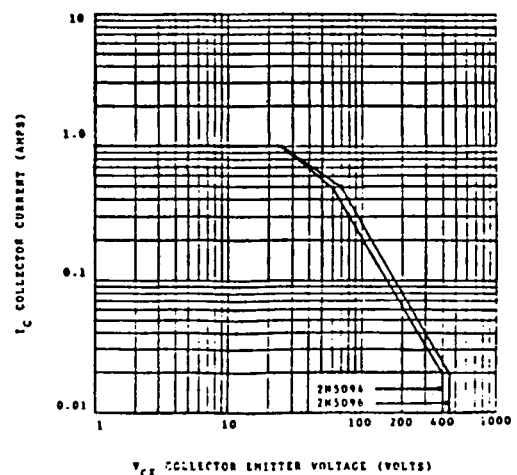
Delay Time	$(V_{CC} = 150 \text{ Vdc},$ $I_C = 100 \text{ mAdc},$ $I_{B1} = I_{B2} = 10 \text{ mAdc})$	t_d	700	ns
Rise Time		t_r	1500	ns
Storage Time		t_s	3	us
Fall Time		t_f	200	ns

*Pulse Test: Pulse width = 300 us, DutyCycle = 2%

TYPICAL OPERATING CURVES



FORWARD BIAS DC SAFE OPERATION AREA (S.O.A. CURVE)
CURVES APPLY BELOW RATED V_{CEO} $T_C = 25^\circ\text{C}$



SSDII SOLID STATE DEVICES, INC.